

Daniel B Habersat

List of Publications by Year in Descending Order

Source: <https://exaly.com/author-pdf/7276870/daniel-b-habersat-publications-by-year.pdf>

Version: 2024-04-26

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

43
papers

1,125
citations

16
h-index

33
g-index

44
ext. papers

1,292
ext. citations

0.9
avg, IF

4.36
L-index

#	Paper	IF	Citations
43	Towards a Robust Approach to Threshold Voltage Characterization and High Temperature Gate Bias Qualification 2020 ,		1
42	Permanent and Transient Effects of High-Temperature Bias Stress on Room- Temperature V_{T} Drift Measurements in SiC Power MOSFETs 2019 ,		4
41	Influence of High-Temperature Bias Stress on Room-Temperature VT Drift Measurements in SiC Power MOSFETs. <i>Materials Science Forum</i> , 2019 , 963, 757-762	0.4	2
40	Measurement considerations for evaluating BTI effects in SiC MOSFETs. <i>Microelectronics Reliability</i> , 2018 , 81, 121-126	1.2	21
39	SiC MOSFET threshold-stability issues. <i>Materials Science in Semiconductor Processing</i> , 2018 , 78, 32-37	4.3	26
38	Influences of Bias Interruption and Reapplication on High-Temperature Threshold-Voltage Shifts of SiC DMOSFETs. <i>Materials Science Forum</i> , 2018 , 924, 743-747	0.4	2
37	Feasibility of SiC Threshold Voltage Drift Characterization for Reliability Assessment in Production Environments. <i>Materials Science Forum</i> , 2017 , 897, 509-512	0.4	8
36	Temperature-dependent threshold stability of COTS SiC MOSFETs during gate switching 2017 ,		7
35	Measurement Issues Affecting Threshold-Voltage Instability Characterization of SiC MOSFETs. <i>Materials Science Forum</i> , 2016 , 858, 461-464	0.4	6
34	Threshold-voltage bias-temperature instability in commercially-available SiC MOSFETs. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 04EA03	1.4	37
33	Comparison of Test Methods for Proper Characterization of VT in SiC MOSFETs. <i>Materials Science Forum</i> , 2016 , 858, 833-839	0.4	14
32	Evaluations of threshold voltage stability on COTS SiC DMOSFETs using fast measurements 2016 ,		14
31	Threshold-Voltage Instability in SiC MOSFETs Due to Near-Interfacial Oxide Traps. <i>Materials Science Forum</i> , 2016 , 858, 585-590	0.4	2
30	Bias-Temperature-Stress Response of Commercially-Available SiC Power MOSFETs. <i>Materials Science Forum</i> , 2015 , 821-823, 677-680	0.4	4
29	Simulating the Influence of Mobile Ionic Oxide Charge on SiC MOS Bias-Temperature Instability Measurements. <i>Materials Science Forum</i> , 2015 , 821-823, 697-700	0.4	1
28	Basic Mechanisms of Threshold-Voltage Instability and Implications for Reliability Testing of SiC MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 316-323	2.9	225
27	A Study of High Temperature DC and AC Gate Stressing on the Performance and Reliability of Power SiC MOSFETs. <i>Materials Science Forum</i> , 2013 , 740-742, 549-552	0.4	11

26	Evaluation of PBTS and NBTS in SiC MOS Using In Situ Charge Pumping Measurements. <i>Materials Science Forum</i> , 2013 , 740-742, 545-548	0.4	12
25	Simulating ion transport and its effects in silicon carbide power MOSFET gate oxides 2013 ,		3
24	Detection of Mobile Ions in the Presence of Charge Trapping in SiC MOS Devices. <i>Materials Science Forum</i> , 2012 , 717-720, 461-464	0.4	10
23	Two-Way Tunneling Model of Oxide Trap Charging and Discharging in SiC MOSFETs. <i>Materials Science Forum</i> , 2012 , 717-720, 465-468	0.4	32
22	Charge Trapping in Sic Power MOSFETs and its Consequences for Robust Reliability Testing. <i>Materials Science Forum</i> , 2012 , 717-720, 1085-1088	0.4	11
21	(Invited) Effect of Threshold-Voltage Instability on SiC Power MOSFET High-Temperature Reliability. <i>ECS Transactions</i> , 2011 , 41, 203-214	1	16
20	Application of reliability test standards to SiC Power MOSFETs 2011 ,		46
19	Investigation of a high temperature oxide-trap activation model for SiC power MOSFETs 2011 ,		3
18	High-Temperature Reliability of SiC Power MOSFETs. <i>Materials Science Forum</i> , 2011 , 679-680, 599-602	0.4	36
17	Improved Observation of SiC/SiO ₂ Oxide Charge Traps Using MOS C-V. <i>Materials Science Forum</i> , 2011 , 679-680, 366-369	0.4	8
16	(Invited) Implications for Robust Reliability Testing of Power SiC MOSFETs. <i>ECS Transactions</i> , 2011 , 41, 215-224	1	
15	Effect of ON-State Stress on SiC DMOSFET Subthreshold I-V Characteristics. <i>Materials Science Forum</i> , 2010 , 645-648, 983-986	0.4	9
14	Implications of Threshold-Voltage Instability on SiC DMOSFET Operation. <i>Materials Science Forum</i> , 2009 , 615-617, 809-812	0.4	6
13	Improvements in SiC MOS Processing as Revealed by Studies of Fixed and Oxide Trap Charge. <i>Materials Science Forum</i> , 2009 , 615-617, 769-772	0.4	3
12	Characterization of Transient Gate Oxide Trapping in SiC MOSFETs Using Fast ΔV_g Techniques. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 2004-2012	2.9	94
11	A Physical Model of High Temperature 4H-SiC MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 2029-2040	2.9	109
10	Time Dependence of Bias-Stress-Induced SiC MOSFET Threshold-Voltage Instability Measurements. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 1835-1840	2.9	205
9	Temperature-Dependence of SiC MOSFET Threshold-Voltage Instability. <i>Materials Science Forum</i> , 2008 , 600-603, 807-810	0.4	32

8	The Effect of Nitridation on SiC MOS Oxides as Evaluated by Charge Pumping. <i>Materials Science Forum</i> , 2008 , 600-603, 743-746	0.4	17
7	Investigation of Drain Current Saturation in 4H-SiC MOSFETs. <i>Materials Science Forum</i> , 2007 , 556-557, 811-814	0.4	
6	Advances in pulsed-laser-deposited AlN thin films for high-temperature capping, device passivation, and piezoelectric-based RF MEMS/NEMS resonator applications. <i>Journal of Electronic Materials</i> , 2006 , 35, 777-794	1.9	18
5	Bias Stress-Induced Threshold-Voltage Instability of SiC MOSFETs. <i>Materials Science Forum</i> , 2006 , 527-529, 1317-1320	0.4	39
4	On Separating Oxide Charges and Interface Charges in 4H-SiC Metal-Oxide-Semiconductor Devices. <i>Materials Science Forum</i> , 2006 , 527-529, 1007-1010	0.4	10
3	Determination of the Temperature and Field Dependence of the Interface Conductivity Mobility in 4H-SiC/SiO ₂ . <i>Materials Science Forum</i> , 2006 , 527-529, 1055-1058	0.4	2
2	Time-Dependent Bias Stress-Induced Instability of SiC MOS Devices. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 911, 5		16
1	Using a First Principles Coulomb Scattering Mobility Model for 4H-SiC MOSFET Device Simulation. <i>Materials Science Forum</i> , 2006 , 527-529, 1321-1324	0.4	3